



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Naoyuki TAKAHASHI et al.

Serial No. 09/767,154

Filed: January 23, 2001

For: CRYSTAL THIN FILM AND
PRODUCTION METHOD THEREFOR

Art Unit: 1765

Examiner: Matthew J. Song

Atty. Docket No. 31721-169084

Customer No.



26694

PATENT TRADEMARK OFFICE

STATEMENT OF HISASHI INOGUCHI

RECEIVED

Assistant Commissioner of Patents and Trademarks
Washington, D.C. 20231

DEC 30 2002

TC 1700

Sir:

I, HISASHI INOGUCHI, sent a substitute specification to the law office of Venable for the subject application. I am the agent for the applicants in Japan.

I am conversant in both the Japanese and English languages.

The presentation of the substitute specification is to conform the specification to the drawings of the application filed in the U.S. and identified above. I further state that the substitute specification contains no new matter. In the application drawings the word "quartz" is used; please see Figure 6. However in translation of the Japanese language specification, the Japanese word for "quartz" may also refer to crystal. This is evidenced by comparing the terms on Figure 6 referring to quartz to the terms in the specification describing Figure 6 which refers to employs the word 'crystal' Example 2, at page 15 line 8 thereof.

Amorphous silicon dioxide and single crystalline silicon dioxide (quartz) can be represented by the same chemical formula "SiO₂". However, single crystalline silicon dioxide has completely different physical characteristics from that of amorphous silicon dioxide. Amorphous silicon dioxide has only insulating properties and amorphous silicon dioxide thin film is often used as an insulation film for semiconductor devices. On the other hand single crystalline silicon dioxide has resonance and piezo electric characteristics.

Accordingly, it appears that the changes presented in the substitute specification are not only supported by the case as originally filed, and thus do no constitute new matter, but also will enrich the art by the disclosure as presented therein.

I further declare that all statements herein are made with the knowledge that willful false statements may jeopardize the validity of any U.S. patent issuing on the U.S. application and/or may result in fine(s) and/or imprisonment.

Date: December 14th 2002

DC2#419602

Hisashi Inoguchi
Hisashi Inoguchi